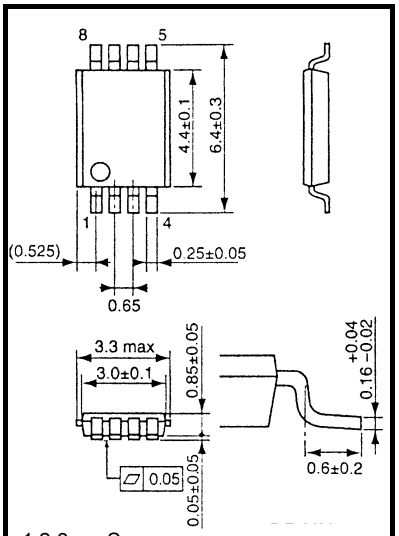
TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (MACH Ⅱ π-MOS Ⅴ)

TPCS8009-H

High-Speed Switching Applications
Switching Regulator Applications
DC/DC Converter Applications

- Low drain-source ON-resistance: $R_{DS\ (ON)}$ = 0.27 Ω (typ.)
- High forward transfer admittance: $|Y_{fs}|$ = 2.1 S (typ.)
- Low leakage current: I_{DSS} = 100 μA (max) (V_{DS} = 150 V)
- Enhancement model: V_{th} = 2.0~4.0 V (V_{DS} = 10 V, I_D = 1 mA)

Unit: mm



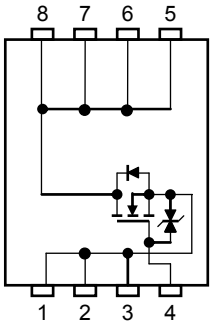
1.2.3.	Source
4	Gate
5.6.7.8	Drain
JEDEC	—
JEITA	—
TOSHIBA	2-3R1F

Weight: 0.036 g (typ.)

Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	150	V
Drain-gate voltage (R_{GS} = 20 kΩ)		V_{DGR}	150	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	DC (Note 1)	I_D	2.1	A
	Pulse (Note 1)	I_{DP}	8.4	
Drain power dissipation (t = 10 s) (Note 2a)		P_D	1.5	W
Drain power dissipation (t = 10 s) (Note 2b)		P_D	0.6	
Single-pulse avalanche energy(Note3)		E_{AS}	3	mJ
Avalanche current		I_{AR}	2.1	A
Repetitive avalanche energy (Note2a, Note 4)		E_{AR}	0.15	mJ
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	−55~150	°C

Circuit Configuration



Note: For Notes 1 to 4, refer to the next page.

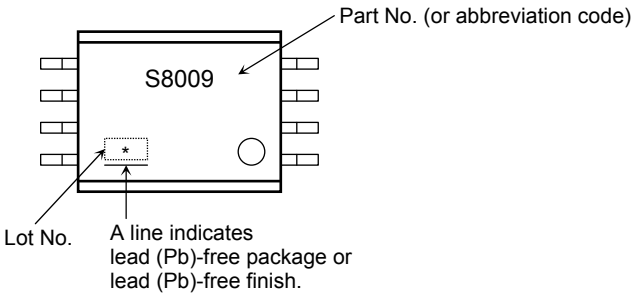
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	$R_{th\ (ch\text{-}a)}$	83.3	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	$R_{th\ (ch\text{-}a)}$	208	°C/W

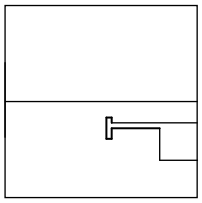
Marking (Note 5)



Note 1: The channel temperature should not exceed 150°C during use.

Note 2:

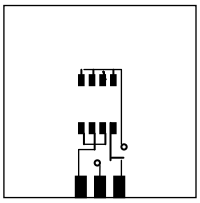
a) Device mounted on a glass-epoxy board (a)



FR-4
25.4 × 25.4 × 0.8
(unit: mm)

(a)

b) Device mounted on a glass-epoxy board (b)



FR-4
25.4 × 25.4 × 0.8
(unit: mm)

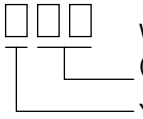
(b)

Note 3: V_{DD} = 50 V, T_{ch} = 25°C (initial), L = 1.0 mH, R_G = 25 Ω, I_{AR} = 2.1 A

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: ○ on the lower right of the marking indicates Pin 1.

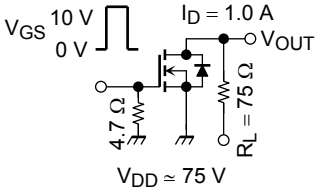
* Weekly code: (Three digits)



Week of manufacture
(01 for first week of year, continuing up to 52 or 53)

Year of manufacture
(The last digit of the calendar year)

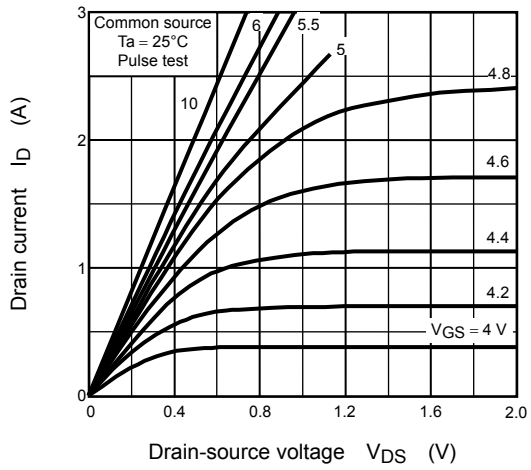
Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	V_{GS} = ±16 V, V_{DS} = 0 V	—	—	±10	μA
Drain cutoff current		I_{DSS}	V_{DS} = 150 V, V_{GS} = 0 V	—	—	100	μA
Drain-source breakdown voltage		$V_{(BR)\ DSS}$	I_D = 10 mA, V_{GS} = 0 V	150	—	—	V
		$V_{(BR)\ DSX}$	I_D = 10 mA, V_{GS} = −5 V	150	—	—	
		$V_{(BR)\ DSX}$	I_D = 10 mA, V_{GS} = −20 V	100	—	—	
Gate threshold voltage		V_{th}	V_{DS} = 10 V, I_D = 1 mA	2.0	—	4.0	V
Drain-source ON-resistance		$R_{DS\ (ON)}$	V_{GS} = 10 V, I_D = 1.0 A	—	0.27	0.35	Ω
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = 10 V, I_D = 1.0 A	0.9	2.1	—	S
Input capacitance		C_{iss}	V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz	—	600	—	pF
Reverse transfer capacitance		C_{rss}		—	20	—	pF
Output capacitance		C_{oss}		—	220	—	pF
Switching time	Rise time	t_r		—	35	—	ns
	Turn-on time	t_{on}		—	95	—	
	Fall time	t_f		—	20	—	
	Turn-off time	t_{off}	Duty ≦ 1%, t_w = 10 μs	—	120	—	
Total gate charge (gate-source plus gate-drain)		Q_g	V_{DD} ≃ 120V, V_{GS} = 10 V, I_D = 2.1 A	—	10	—	nC
Gate-source charge		Q_{gs}		—	7.5	—	nC
Gate-drain (“Miller”) charge		Q_{gd}		—	2.5	—	nC
Gate switch charge		Q_{sw}		—	3.3	—	nC

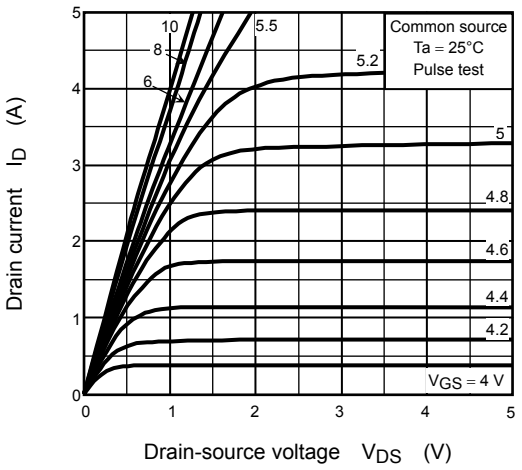
Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current (pulse) (Note 1)	I_{DRP}	—	—	—	8.4	A
Forward voltage (diode)	V_{DSF}	I_{DR} = 2.1 A, V_{GS} = 0 V	—	—	−2.0	V

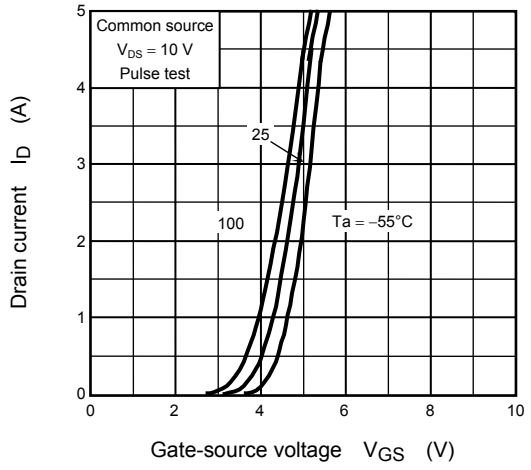
$I_D - V_{DS}$



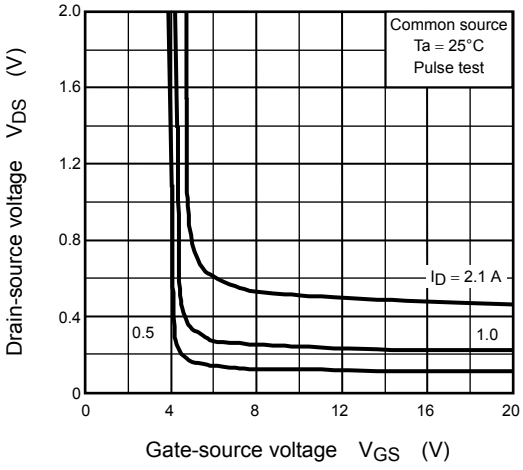
$I_D - V_{DS}$



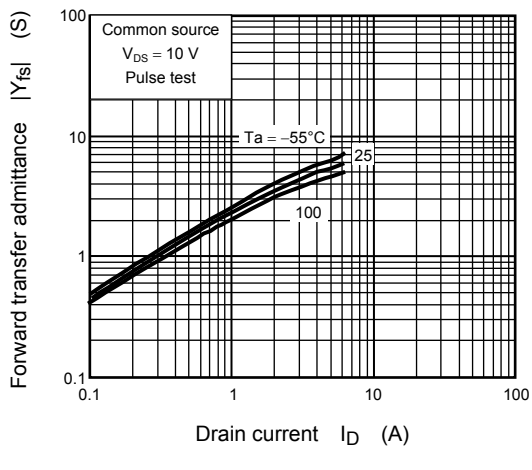
$I_D - V_{GS}$



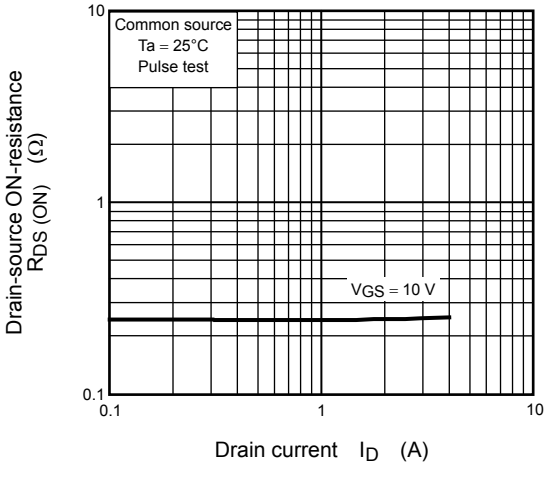
$V_{DS} - V_{GS}$



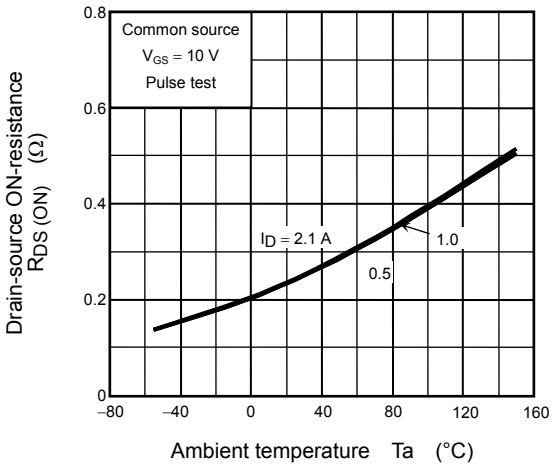
$|Y_{fs}| - I_D$



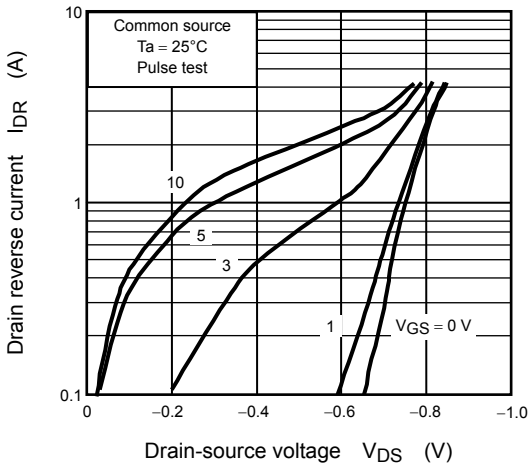
$R_{DS\ (ON)} - I_D$



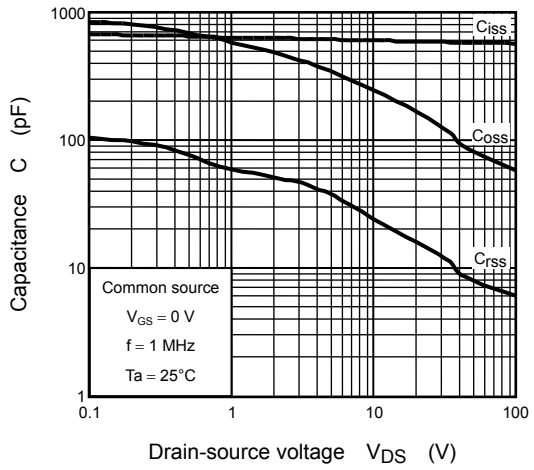
$R_{DS\ (ON)}$ – Ta



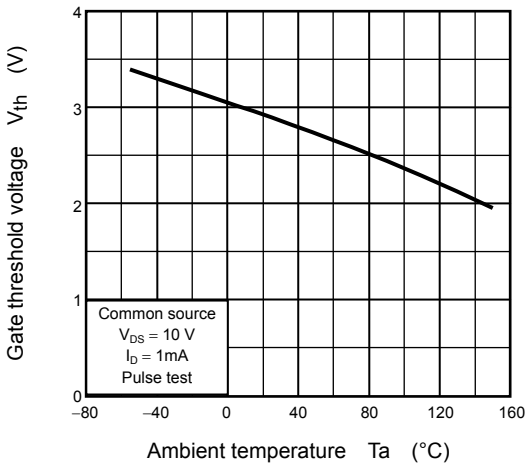
I_{DR} – V_{DS}



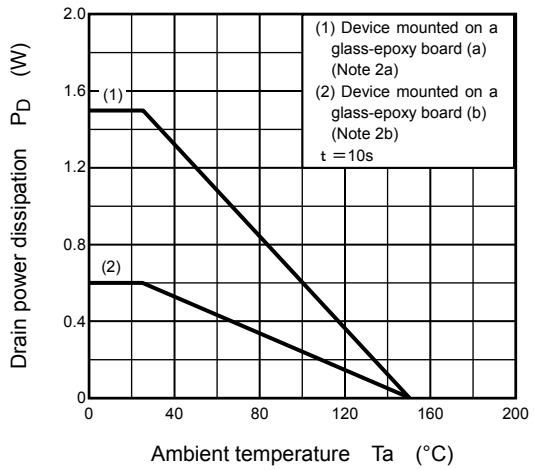
Capacitance – V_{DS}



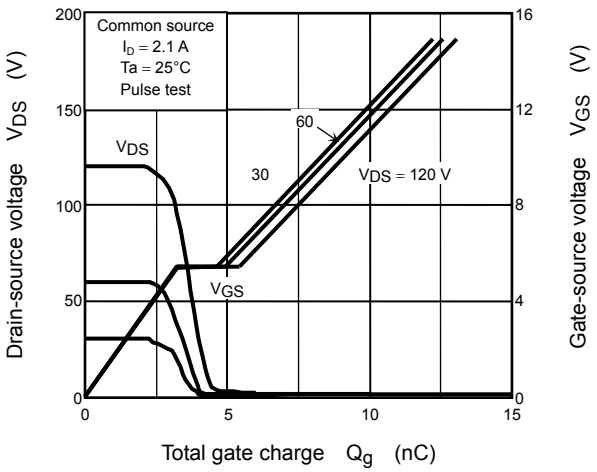
V_{th} – Ta

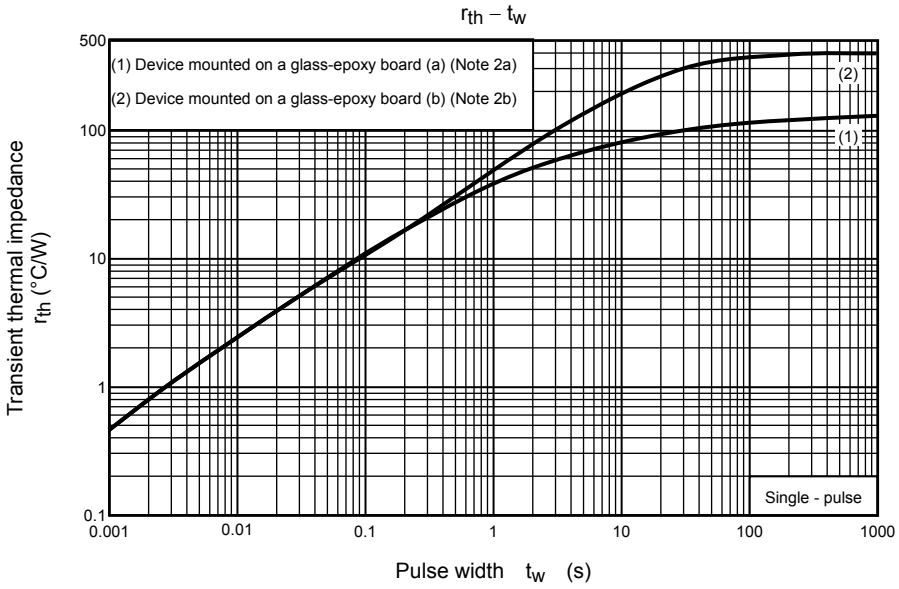


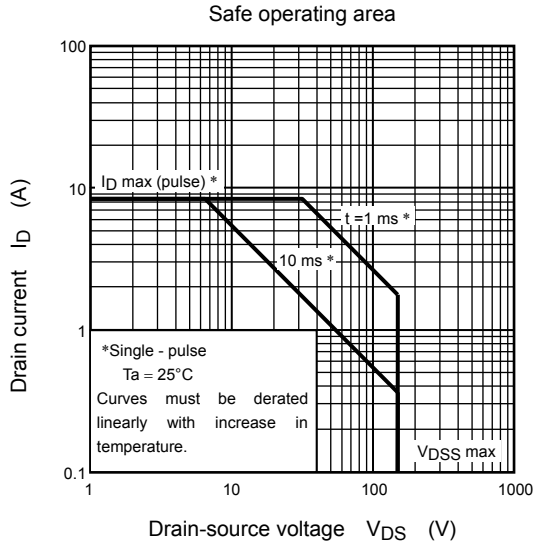
P_D – Ta



Dynamic input/output characteristics




$r_{th} - t_w$
(1) Device mounted on a glass-epoxy board (a) (Note 2a)
(2) Device mounted on a glass-epoxy board (b) (Note 2b)
(2)
(1)
Single - pulse
Transient thermal impedance r_{th} (°C/W)
500
100
10
1
0.1
0.001
0.01
0.1
1
10
100
1000
Pulse width t_w (s)


Safe operating area
I_D max (pulse) *
t =1 ms *
10 ms *
*Single - pulse
Ta = 25°C
Curves must be derated linearly with increase in temperature.
V_{DSS} max
Drain current I_D (A)
100
10
1
0.1
1
10
100
1000
Drain-source voltage V_{DS} (V)

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20070701-EN

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